TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π–MOSIII)

# 2SK2717

## DC-DC Converter and Motor Drive Applications

• Low drain-source ON resistance : RDS (ON) =  $2.3 \Omega$  (typ.)

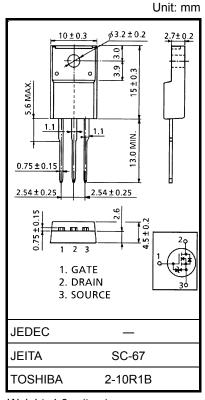
• High forward transfer admittance  $: |Y_{fs}| = 4.4 \text{ S (typ.)}$ 

Low leakage current  $: I_{DSS} = 100 \,\mu\text{A} \text{ (max) (V}_{DS} = 720 \,\text{V)}$ 

• Enhancement mode :  $V_{th} = 2.0 \text{ to } 4.0 \text{ V (Vps} = 10 \text{ V, Ip} = 1 \text{ mA)}$ 

## **Absolute Maximum Ratings (Ta = 25°C)**

| Characteris             | stics                  | Symbol           | Rating     | Unit |  |
|-------------------------|------------------------|------------------|------------|------|--|
| Drain-source voltage    |                        | $V_{DSS}$        | 900        | V    |  |
| Drain-gate voltage (Ro  | <sub>SS</sub> = 20 kΩ) | $V_{DGR}$        | 900        | V    |  |
| Gate-source voltage     |                        | V <sub>GSS</sub> | ±30        | V    |  |
| Drain current           | DC (Note 1)            | I <sub>D</sub>   | 5          | Α    |  |
|                         | Pulse (Note 1)         | I <sub>DP</sub>  | 15         | A    |  |
| Drain power dissipation | n (Tc = 25°C)          | $P_{D}$          | 45         | W    |  |
| Single pulse avalanche  | e energy<br>(Note 2)   | E <sub>AS</sub>  | 595        | mJ   |  |
| Avalanche current       |                        | I <sub>AR</sub>  | 5          | Α    |  |
| Repetitive avalanche e  | nergy (Note 3)         | E <sub>AR</sub>  | 4.5        | mJ   |  |
| Channel temperature     |                        | T <sub>ch</sub>  | 150        | °C   |  |
| Storage temperature ra  | inge                   | T <sub>stg</sub> | -55 to 150 | °C   |  |



Weight: 1.9 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

| Characteristics                        | Symbol                 | Max  | Unit |
|--|------------------------|------|------|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 2.78 | °C/W |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 62.5 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 43.6 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 5 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.



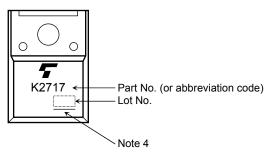
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| Charac  | cteristics      | Symbol               | Test Condition  | Min | Тур. | Max | Unit |
|---|-----------------|----------------------|---|-----|------|-----|------|
| Gate leakage cu                                 | ırrent          | I <sub>GSS</sub>     | V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V                              | _   | _    | ±10 | μΑ   |
| Gate-source bro                                 | eakdown voltage | V (BR) GSS           | $I_G = \pm 10 \mu A, V_{DS} = 0 V$  | ±30 | _    | _   | V    |
| Drain cut-off cu                                | rrent           | I <sub>DSS</sub>     | V <sub>DS</sub> = 720 V, V <sub>GS</sub> = 0 V                              | _   | _    | 100 | μA   |
| Drain-source br                                 | eakdown voltage | V (BR) DSS           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V                               | 900 | _    | _   | V    |
| Gate threshold v                                | /oltage         | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA                               | 2.0 | _    | 4.0 | V    |
| Drain-source O                                  | N resistance    | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.0 A                              | _   | 2.3  | 2.5 | Ω    |
| Forward transfe                                 | r admittance    | Y <sub>fs</sub>      | V <sub>DS</sub> = 20 V, I <sub>D</sub> = 3.0 A                              | 1.1 | 4.4  | _   | S    |
| Input capacitano                                | ce              | C <sub>iss</sub>     |   | _   | 1200 | _   |      |
| Reverse transfer capacitance                    |                 | C <sub>rss</sub>     | V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz                    | _   | 20   | _   | pF   |
| Output capacitance                              |                 | Coss                 |   | _   | 120  | _   |      |
| Switching time                                  | Rise time       | t <sub>r</sub>       | $V_{GS} = 10V$ $V_{GS} = 10V$ $V_{OUT}$ $V_{OUT}$ $V_{OUT}$ $V_{DD} = 200V$ | -   | 40   | _   |      |
|   | Turn-on time    | t <sub>on</sub>      |   | -   | 90   | _   | ns   |
|   | Fall time       | t <sub>f</sub>       |   | -   | 60   | _   | 115  |
|   | Turn-off time   | t <sub>off</sub>     | Duty $\leq 1\%$ , $t_{\rm W} = 10 \mu \rm s$                                | _   | 200  | _   |      |
| Total gate charge (gate-source plus gate-drain) |                 | Qg                   |   | _   | 45   | _   |      |
| Gate-source charge                              |                 | Q <sub>gs</sub>      | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$    |     | 25   | _   | nC   |
| Gate-drain ("miller") Charge                    |                 | Q <sub>gd</sub>      |   | _   | 20   | _   |      |

# Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol           | Test Condition                               | Min | Тур. | Max  | Unit |
|---|------------------|--|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub>  | _  | _   | _    | 5    | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | _  | _   | _    | 15   | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V | _   | _    | -1.9 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V | _   | 1300 | 1    | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>  | dl <sub>DR</sub> / dt = 100 A / μs           | _   | 11   |      | μC   |

# Marking

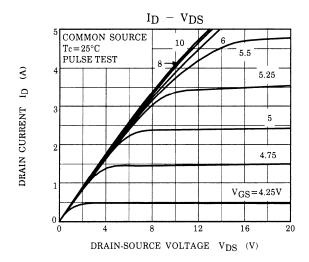


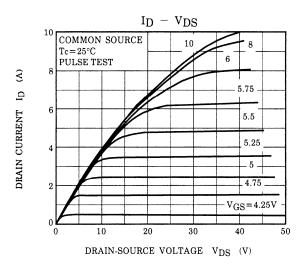
Note 4: A line under a Lot No. identifies the indication of product Labels.

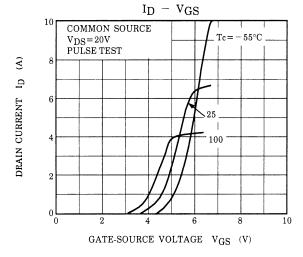
Not underlined: [[Pb]]/INCLUDES > MCV

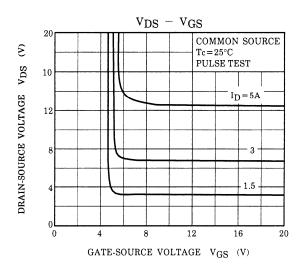
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

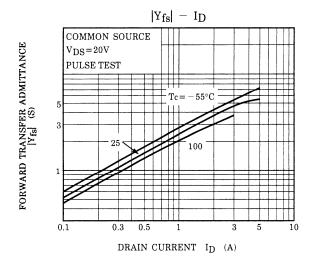
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

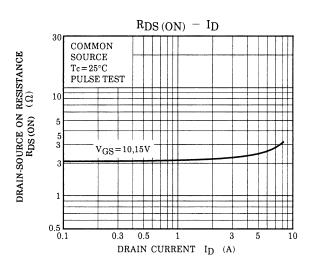




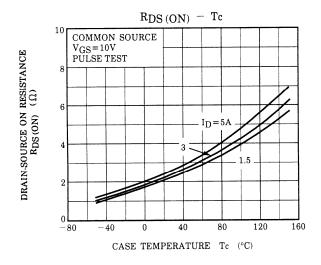


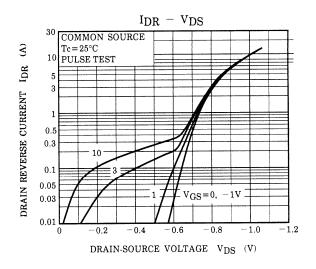


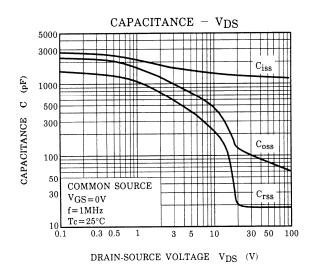


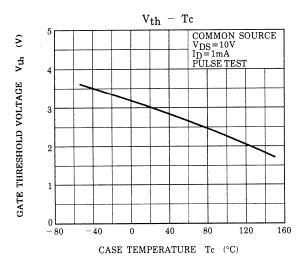


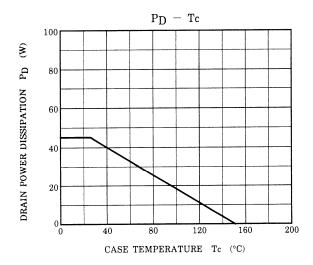
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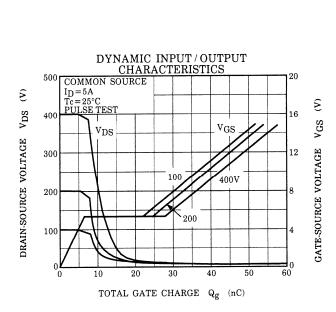




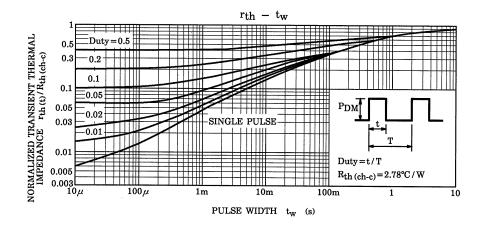


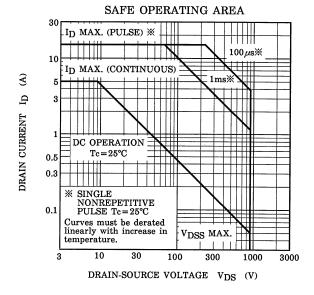


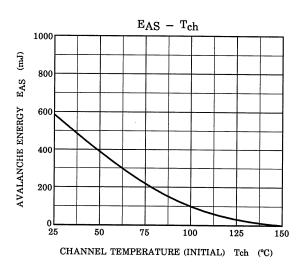


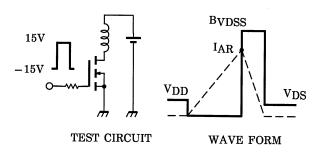


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$$\begin{aligned} &RG = 25~\Omega \\ &V_{DD} = 90~V,~L = 43.6~mH \end{aligned} \qquad EAS = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - VDD} \right)$$

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